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## Technology development of CMOS Image sensors

After a basic review of the working principles of CMOS image sensor (pinned photodiode device), the main technologies and process modules (such as Back-Side Illumination, integrated lightguides and anti-reflective coatings, buried light shields, hybrid bonding) used in the manufacturing of CMOS Image Sensors (CIS) will be described, focusing on their correlation with the performance of pixel array. The impact of metal contamination in manufacturing line in terms of photodiode dark current will be also briefly covered.

### Summary

**Presenter:** DEL MONTE, Andrea (LFoundry)

**Session Classification:** Invited